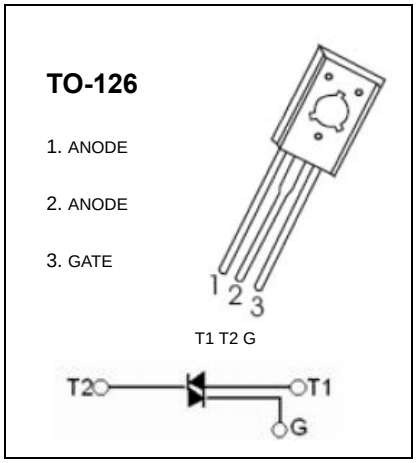
SHENZHEN HAOCHANG SEMICONDUCTOR CO.,LTD.

TO-126 Plastic-Encapsulate Thyristors

BT134 TRIAC



FEATURES

Glass passivated triacs in a plastic, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.
Typical applications include motor control, industrial and domestic lighting , heating and static switching.

MAXIMUM RATINGS(T_a=25℃ unless otherwise noted)

Symbol Para	meter	Test conditions	Value	Unit
V_{DRM}/V_{RRM}	Repetitive peak off-state/reverse voltages		600	V
$I_{T(RMS)}$	RMS on-state current Non-repetitive peak on-state current	full sine wave ;Tmb≦107℃	4	A
I^2t	I^2t for fusing	t=10ms	3.1	A^2s
dI_T/dt	Repetitive rate of rise of on-state current after tiggering	dI_G/dt=0.2A/us		
		T2+G+	50	A/us
		T2+G-	50	A/us
		T2-G-	50	A/us
		T2-G+	10	A/us
I_{GM}	Peak gate current		2	A
V_{GM}	Peak gate voltage		5	V
P_{GM}	Peak gate power		5	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	0.5	W
T_{stg}	Storage Temperature		-40~150	℃
T_j	Operating junction Temperature		125	℃

ELECTRICAL CHAR ACTERISTICS(T_a=25℃ unles s other wise specifie d)

Parameter		Symbol	Test conditions		Min	Typ	Max	Unit
Rated repetitive peak off-state current		I_{DRM}	$V_D=V_{DRM}$				10	μA
On-state voltage		V_{TM}	I_T=3A			1.4	1.7	V
Gate trigger current		I_{GT}	T_2(+), G(+)	V_D=12V			7	mA
			T_2(+), G(-)				7	mA
			T_2(-), G(-)	R_L=100Ω			7	mA
			T_2(-), G(+)				20	mA
Gate trigger voltage		V_{GT}	T_2(+), G(+)	V_D=12V			1.45	V
			T_2(+), G(-)				1.45	V
			T_2(-), G(-)	R_L=100Ω			1.45	V
			T_2(-), G(+)				2	V
Holding current		I_H	I_T=100mA I_G=20mA				15	mA
Thermal Resistance Junction to mounting base		$R_{th\ j\text{-}mb}$	full cycle				3.0	K/W
			half cycle				3.7	K/W
Thermal Resistance Junction to ambient		$R_{th\ j\text{-}a}$	In free air			60		K/W